

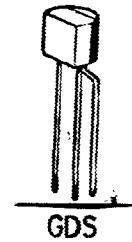
MICRO ELECTRONICS

N-CHANNEL
JUNCTION
FET

DESCRIPTION

BF245 is N-Channel Junction Field Effect Transistor designed for VHF/UHF amplifiers and mixer.

TO-92



ABSOLUTE MAXIMUM RATINGS

Drain-Source Voltage	VDS	30V
Drain-Gate Voltage	VDG	30V
Gate-Source Voltage	VGS	30V
Drain Current	ID	25mA
Gate Current	IG	10mA
Total Power Dissipation	Ptot	300mW
Operating & Storage Junction Temperature	Tj, Tstg	-65 to +150°C

ELECTRO-OPTICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	CONDITIONS		
Gate-Source Breakdown Voltage	BVGSS	30		V	IG=1μA	VDS=0	
Gate Leakage Current	IGSS		5	nA	VGS=20V	VDS=0	
Drain Current	A IDSS	2	6.5	mA	VDS=15V	VGS=0	
		B	6	15			mA
		C	12	25			mA
Gate-Source Voltage	A VGS	0.4	2.2	V	VDS=15V	ID=200μA	
		B	1.6	3.8			V
		C	3.2	7.5			V
Gate-Source Cutoff Current	VGS(off)	0.5	8	V	VDS=15V	ID=10nA	
Forward Transfer Admittance	Yfs	3	6.5	mmho	VDS=15V	VGS=0 f=1kHz	
Feedback Capacitance	Ciss		4	pF	VDS=20V		
Input Capacitance	Crss		1.1	pF	VGS=1V		
Output Capacitance	Coss		1.6	pF	f=1MHz		

* Pulse test : pulse width < 300μs, duty cycle < 2%.



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